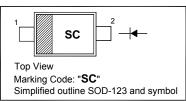
Surface Mount Schottky Barrier Diode

Features

- Very low forward voltage
- · High Current Capability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T₂ = 25 °C)

Absolute Maximum Natings (1 _a = 25°C)			
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RRM}	20	V
Working Peak Reverse Voltage	V_{RWM}	20	V
DC Reverse Voltage	V_R	20	V
Average Rectified Forward Current	I _{F(AV)}	0.5	Α
Non-Repetitive Peak Forward Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	5.5	А
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	340	°C/W
Thermal Resistance Junction to Lead	$R_{\theta JL}$	150	°C/W
Junction Temperature	Tj	- 65 to + 150	°C
Storage Temperature	T _{stg}	- 65 to + 150	°C

¹⁾ Following any rated load condition and with rated V_{RRM} applied.

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$ at $I_F = 0.5 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$ at $I_F = 0.1 \text{ A}$, $T_j = 100 ^{\circ}\text{C}$ at $I_F = 0.5 \text{ A}$, $T_j = 100 ^{\circ}\text{C}$	V _F	0.375 0.44 0.26 0.36	V
Reverse Current at $V_R = 10 \text{ V}$, $T_j = 25 ^{\circ}\text{C}$ at $V_R = 20 \text{ V}$, $T_j = 25 ^{\circ}\text{C}$ at $V_R = 10 \text{ V}$, $T_j = 100 ^{\circ}\text{C}$ at $V_R = 20 \text{ V}$, $T_j = 100 ^{\circ}\text{C}$	I _R	40 150 3 7	μΑ μΑ mA mA
Total Capacitance at V_R = 5 V (test signal range 100 KHz to 1 MHz), T_j = 25 °C	C _{tot}	110	pF











Dated: 04/04/2011 Rev:02

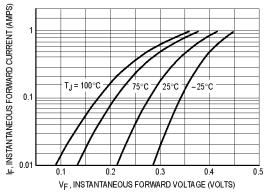


Figure 1. Typical Forward Voltage

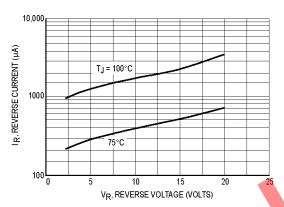


Figure 2. Typical Reverse Current

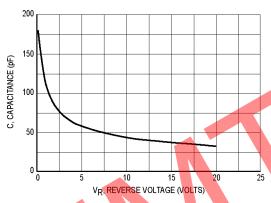


Figure 3. Typical Capacitance

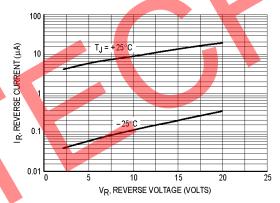


Figure 4. Typical Reverse Current

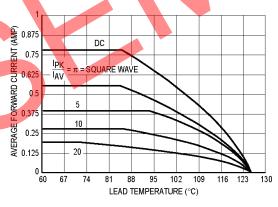


Figure 5. Current Derating (Lead)

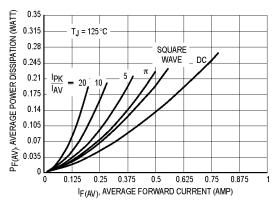


Figure 6. Power Dissipation











PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123

